

Page 25, line 1, change "dyne/cm" to read --dyne/cm²--; and
line 7, change "dyne/cm" to read --dyne/cm²--, both
instances.

NE
Page 32, line 18, change "dyne/cm" to read --dyne/cm²--.

Page 33, line 7, change "dyne/cm" to read --dyne/cm²--;
line 10, change "dyne/cm" to read --dyne/cm²--;
line 16, change "dyne/cm" to read --dyne/cm²--; and
line 17, change "dyne/cm" to read --dyne/cm²--.

IN THE CLAIMS:

Please cancel ~~claims~~ 34 and 38 and rewrite claims 33 and 37 as
follows:

33. (amended) ~~A stress-adjusted insulating film forming method for
forming a multilayered insulating film on a substrate, said method
comprising the steps of:~~

- (a) forming a first insulating layer with tensile [a first
type of] stress;
- (b) forming a second insulating layer with compressive [a
second type of] stress[, different from said first type of stress];
- (c) forming a conductive interconnection layer on and in
contact with said second insulating layer; [and]
- (d) forming a third insulating layer with compressive [said
second type of] stress on and in contact with said conductive
interconnection layer; and [.]

Claim 37
~~(e) repeating steps (a) through (d) at least twice to produce a structure containing at least three of said conductive interconnection layers, each of said conductive interconnection layers being sandwiched between and having opposing surfaces in contact with insulating layers having compressive stress.~~

Claim 37
~~37. (amended) A semiconductor device comprising a substrate, a plurality of first and second types of insulating films having, respectively, compressive and tension [different first and second types of] stress formed on said substrate and at least three [a] layers of conductive interconnectors sandwiched between and in contact with insulating films having compressive [the same type of] stress.~~

Claim 40, line 3, delete "dyne/cm" and insert --dyne/cm²--.

REMARKS

The independent claims have now been limited to a method wherein at least three conductive layers are sandwiched between and in contact with insulating layers having compressive stress as shown, for example, in Fig. 10A of the drawings. For an additional discussion of support or description of the invention as now claimed the examiner is referred to the remarks which accompanied the Preliminary Amendment filed November 17, 1999.